

BB506M

Built in Biasing Circuit MOS FET IC **UHF RF Amplifier**

REJ03G1604-0100 Rev.1.00 Nov 26, 2007

Features

- Built in Biasing Circuit; To reduce using parts cost & PC board space.
- High gain

PG = 24 dB typ. (f = 900 MHz)

• Low noise

NF = 1.4 dB typ. (f = 900 MHz)

• Low output capacitance

Coss = 1.1 pF typ. (f = 1 MHz)

• Provide mini mold packages: CMPAK-4 (SOT-343mod)

Outline

RENESAS Package code: PLSP0004ZA-A

(Package name: MPAK-4)



- 1. Source
- 2. Gate1
- 3. Gate2

Notes: 1. Marking is "FS-".

2. BB506M is individual type number of RENESAS BBFET.

Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DS}	6	V
Gate1 to source voltage	V_{G1S}	+6	V
		-0	
Gate2 to source voltage	V _{G2S}	+6	V
		-0	
Drain current	I _D	30	mA
Channel power dissipation	Pch ^{Note3}	300	mW
Channel temperature	Tch	150	°C
Storage temperature	Tstg	−55 to +150	°C

Notes: 3. Value on the glass epoxy board (50 mm \times 40 mm \times 1 mm).

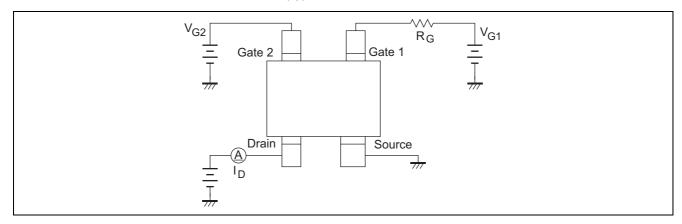
This device is sensitive to electro static discharge. An adequate careful handling procedure is requested.

Electrical Characteristics

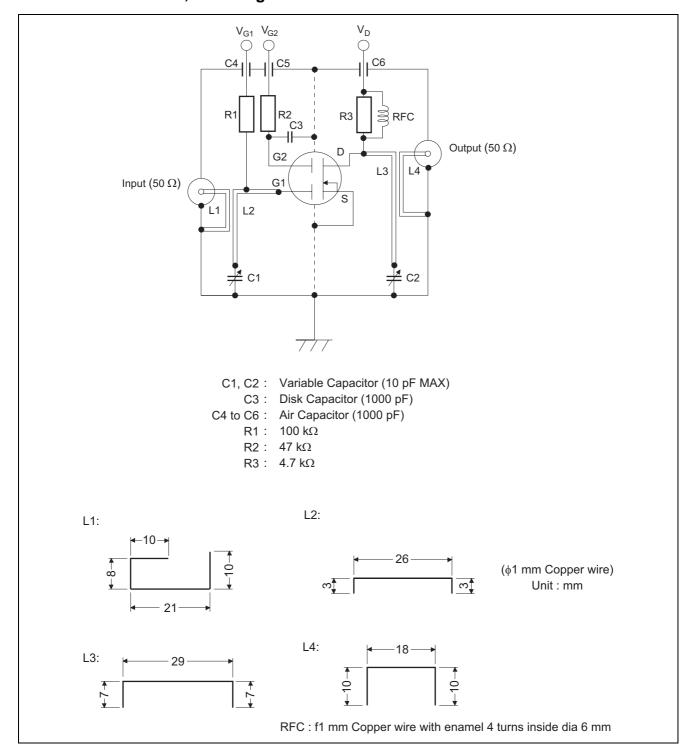
 $(Ta = 25^{\circ}C)$

Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	6	_	_	V	$I_D = 200 \ \mu A, \ V_{G1S} = V_{G2S} = 0$
Gate1 to source breakdown voltage	V _{(BR)G1SS}	+6	_	_	V	$I_{G1} = +10 \ \mu A, \ V_{G2S} = V_{DS} = 0$
Gate2 to source breakdown voltage	V _{(BR)G2SS}	+6	_	_	V	$I_{G2} = +10 \ \mu A, \ V_{G1S} = V_{DS} = 0$
Gate1 to source cutoff current	I _{G1SS}	_	_	+100	nA	$V_{G1S} = +5 \text{ V}, V_{G2S} = V_{DS} = 0$
Gate2 to source cutoff current	I _{G2SS}	_	_	+100	nA	$V_{G2S} = +5 \text{ V}, V_{G1S} = V_{DS} = 0$
Gate1 to source cutoff voltage	V _{G1S(off)}	0.5	0.8	1.1	V	$V_{DS} = 5 \text{ V}, V_{G2S} = 4 \text{ V}, I_{D} = 100 \mu\text{A}$
Gate2 to source cutoff voltage	V _{G2S(off)}	0.4	0.7	1.0	V	$V_{DS} = 5 \text{ V}, V_{G1S} = 5 \text{ V}, I_{D} = 100 \mu\text{A}$
Drain current	I _{D(op)}	12	16	20	mA	$V_{DS} = 5 \text{ V}, V_{G1} = 5 \text{ V}, V_{G2S} = 4 \text{ V}$ $R_G = 100 \text{ k}\Omega$
Forward transfer admittance	y _{fs}	27	32	38	mS	$V_{DS} = 5 \text{ V}, V_{G1} = 5 \text{ V}, V_{G2S} = 4 \text{ V}$ $R_G = 100 \text{ k}\Omega, f = 1 \text{ kHz}$
Input capacitance	C _{iss}	1.2	1.6	2.0	pF	V _{DS} = 5 V, V _{G1} = 5 V, V _{G2S} = 4 V
Output capacitance	Coss	0.7	1.1	1.5	pF	$R_G = 100 \text{ k}\Omega, f = 1 \text{ MHz}$
Power gain	PG	19	24	29	dB	$V_{DS} = 5 \text{ V}, V_{G1} = 5 \text{V}, V_{G2S} = 4 \text{ V}$
Noise figure	NF	_	1.4	2.1	dB	$R_G = 100 \text{ k}\Omega, f = 900 \text{ MHz}$

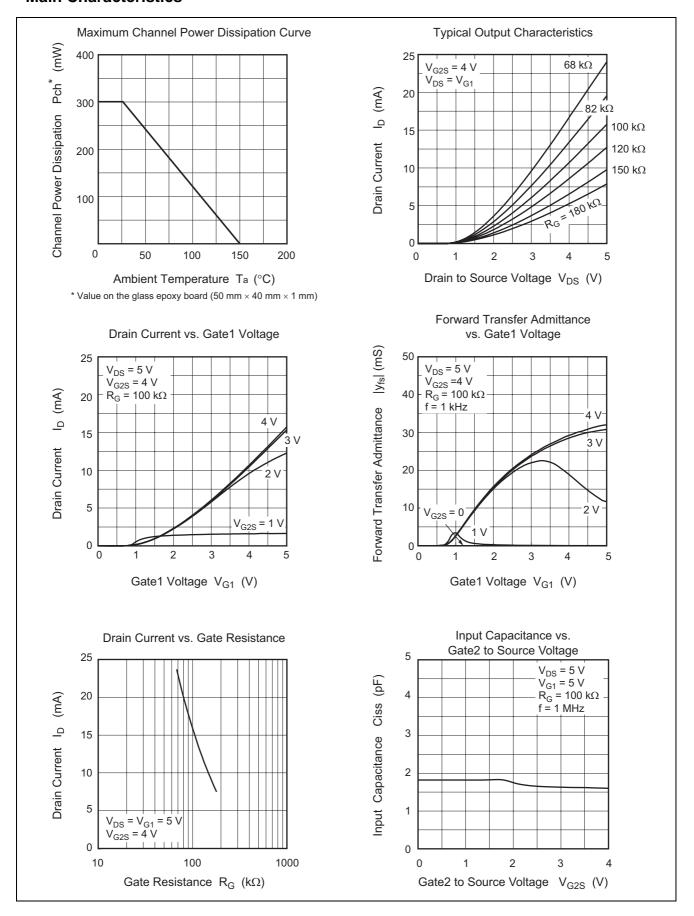
Bias Circuit for Operating Items ($I_{D(op)}$, $|y_{fs}|$, Ciss, Coss, NF, PG)

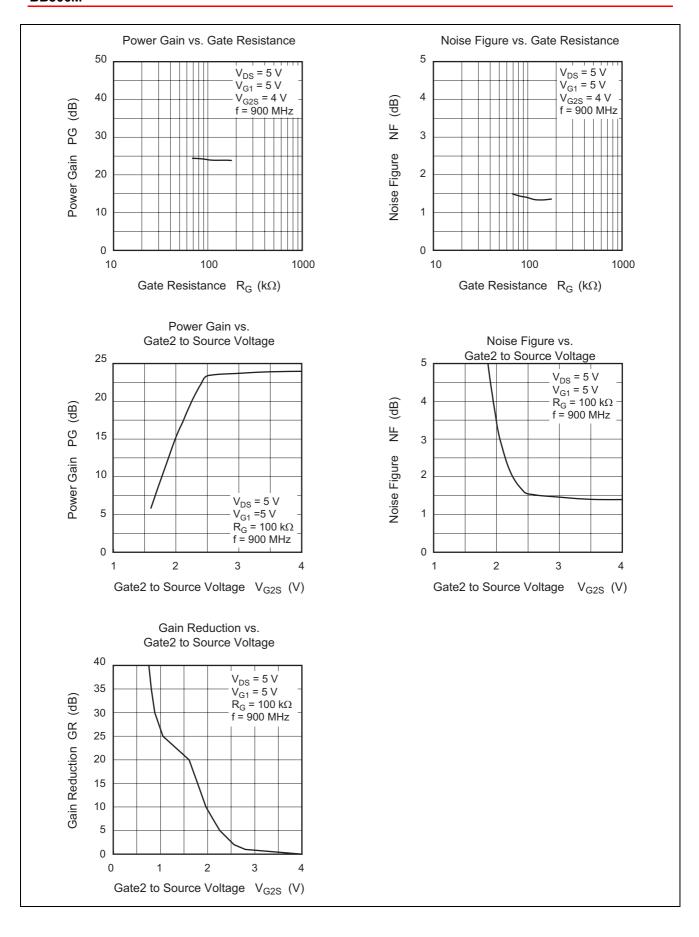


900 MHz Power Gain, Noise Figure Test Circuit

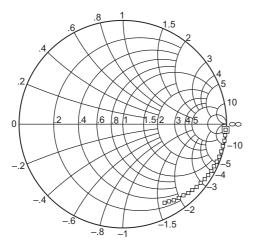


Main Characteristics



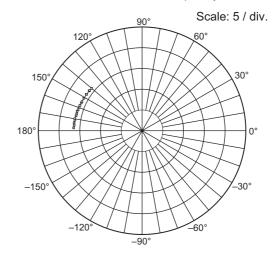


S₁₁ Parameter vs. Frequency



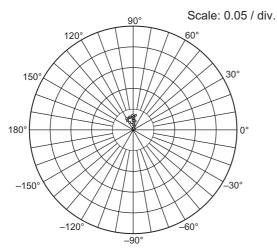
Test condition: V_{DS} = 5 V, V_{G1} = 5 V, V_{GS2} = 4 V, R_G = 100 k Ω 0.05 to 1.05 GHz (0.05 GHz step)

S₂₁ Parameter vs. Frequency



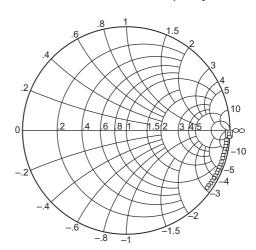
Test condition: V_{DS} = 5 V, V_{G1} = 5 V, V_{G82} = 4 V, R_G = 100 k Ω 0.05 to 1.05 GHz (0.05 GHz step)

S₁₂ Parameter vs. Frequency



Test condition: V_{DS} = 5 V, V_{G1} = 5 V, V_{GS2} = 4 V, R_G = 100 k Ω 0.05 to 1.05 GHz (0.05 GHz step)

S₂₂ Parameter vs. Frequency



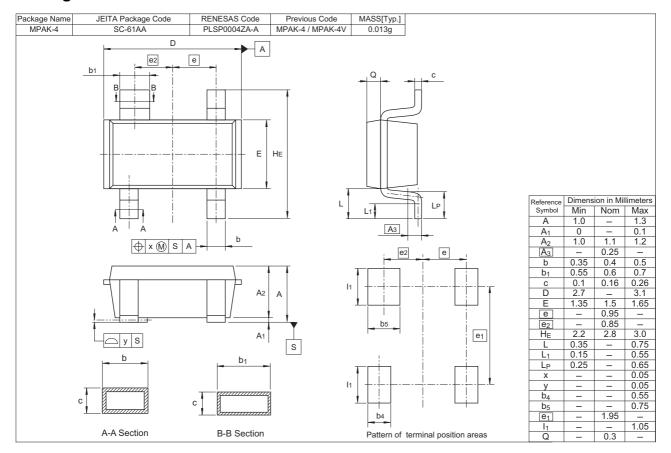
Test condition: VDS = 5 V, VG1 = 5 V, VGS2 = 4 V, R_G = 100 k Ω 0.05 to 1.05 GHz (0.05 GHz step)

S parameter

 $(V_{DS} = 5~V,~V_{G1} = 5~V,~V_{G2S} = 4~V,~R_G = 100~k\Omega,~Zo = 50~\Omega)$

Freq	S11		S21		S	S12		S22	
(MHz)	Mag	Deg	Mag	Deg	Mag	Deg	Mag	Deg	
50	0.995	-3.3	3.28	177.9	0.001	17.6	0.991	-1.8	
100	0.991	-6.2	3.26	175.5	0.001	75.6	0.996	-3.6	
150	0.992	-9.3	3.28	173.7	0.002	73.8	0.995	-5.2	
200	0.987	-12.4	3.26	171.3	0.002	79.5	0.997	-7.0	
250	0.984	-15.5	3.27	170.0	0.004	116.5	0.995	-8.6	
300	0.981	-18.6	3.24	167.3	0.003	89.6	0.993	-10.3	
350	0.975	-21.7	3.23	165.8	0.004	76.3	0.992	-11.8	
400	0.967	-24.8	3.24	163.3	0.004	87.0	0.989	-13.9	
450	0.964	-27.9	3.22	161.9	0.004	91.9	0.991	-15.5	
500	0.958	-30.8	3.22	159.4	0.006	89.0	0.987	-17.0	
550	0.951	-33.9	3.22	157.9	0.006	100.4	0.988	-18.9	
600	0.939	-37.0	3.20	155.4	0.004	84.2	0.985	-20.4	
650	0.933	-40.3	3.20	154.1	0.004	85.4	0.984	-22.2	
700	0.922	-43.5	3.20	150.7	0.007	80.4	0.983	-23.7	
750	0.916	-46.5	3.19	150.7	0.007	93.5	0.981	-25.5	
800	0.900	-49.6	3.19	146.7	0.006	108.8	0.979	-27.2	
850	0.892	-52.8	3.18	146.4	0.005	122.9	0.978	-28.9	
900	0.883	-56.2	3.18	142.8	0.005	120.3	0.975	-30.6	
950	0.866	-59.2	3.17	142.3	0.006	104.0	0.970	-32.3	
1000	0.858	-62.0	3.16	139.8	0.006	121.3	0.970	-33.8	

Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
BB506MFS-TL-E	3000	Emboss Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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